

VERSION OF AMENDMENT WITH MARKINGS TO SHOW CHANGES MADEApplication No.: 09/845,327IN THE SPECIFICATION:

Amend the paragraph beginning on p. 7, line 12, as follows:

An initial description will now be made of how a high-frequency ceramic package according to the embodiment is constructed. FIG. 1 illustrates a ceramic frame plate 12 brazed at the reverse side thereof to a jointed metal plate 11 by means of, e.g., a silver/copper solder. In addition, leads 13 for connection to the outside are brazed to the ceramic frame plate 12 through metallized patterns 14 by means of, e.g., the silver/copper solder. The metallized patterns are formed on the ceramic frame plate 12 on the obverse side thereof. The lead 13 is formed by KV (a Fe-Ni-Co series alloy, called ["Kovar"] "Kovar" as a brand name) or a 42-alloy (a nickel alloy). Then, the brazed metal plate 11, ceramic frame plate 12, and leads 13 are nickel-plated and gold-plated on metal surfaces thereof, thereby forming the ceramic package 10. The substantially rectangular-shaped metal plate 11 is provided with fixing cutouts 15 at both ends of the metal plate 11 in a longitudinal direction thereof for fixing the ceramic package 10. The metal plate 11 is screwed down tight on a fixing member (not shown) at the cutouts 15. In the ceramic package 10, semiconductor electronic components are packaged in a concave cavity 16 on a bottom 16a thereof. The ceramic frame plate 12 has a hollow portion at the central portion thereof. The cavity 16 is defined between the jointed metal plate 11 and the ceramic frame plate 12. Namely, a semiconductor electronic component mounting portion is formed on the bottom 16a of the cavity 16. The package 10

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semiconductor components are then hermetically sealed by means of resin. A metal material forms the bottom 16a is made from a highly heat-sinking material having a high level of thermal conductivity. Such a heat-sinking material includes, e.g., Cu-W (copper-soaked tungsten) and (a jointed plate having three layers of Cu-Mo-Cu). Meanwhile, a low thermal expansion material close to ceramics in thermal expansion coefficient, such as KV and the 42-alloy, forms a peripheral extending metal portion around the bottom 16a, which supports the bottom 16a.

IN THE CLAIMS:

Amend claim 1 as follows:

1. (Amended) A high-frequency ceramic package, comprising:

a first metal plate forming a substantially rectangular shape, said first metal plate having fixing cutouts defined at both ends in a longitudinal direction thereof and further having a hollowed portion formed at a central portion thereof,

a second metal plate being fitted in said hollowed portion of said first metal plate in a relationship in which said first and second metal plates are jointed in [a] an end to end relationship, and

a ceramic frame plate brazed to a jointed metal plate on a peripheral surface of said jointed metal plate, said jointed metal plate including said first and second metal plates,

wherein a cavity defined between said second metal plate and said ceramic frame plate contains a semiconductor electronic component mounting portion on a bottom of said cavity, said first metal plate being close to said ceramic frame plate in thermal expansion coefficient, said second

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plate being made from a material having an elevated degree of heat-sinking characteristic thicknesses of said first and second metal plates being substantially equal, said first and second plates being jointed at substantially the same level, and said second metal plate being a substantial rectangular plate.